## 1. General description

NPN high power bipolar transistor in a power DPAK, TO-252 (SOT428C) Surface-Mounted Device (SMD) plastic package.

PNP complement: MJD45H11A

### 2. Features and benefits

- · High thermal power dissipation capability
- · High energy efficiency due to less heat generation
- · Electrically similar to popular MJD44H series
- Low collector emitter saturation voltage
- Fast switching speeds
- AEC-Q101 qualified

## 3. Applications

- · Power management
- Load switch
- Linear mode voltage regulator
- · Constant current drive backlighting application
- Motor drive
- Relay replacement

### 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage		-	-	80	V
I <sub>C</sub>	collector current		-	-	8	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	16	Α
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1 V; I <sub>C</sub> = 2 A; T <sub>amb</sub> = 25 °C	60	-	-	



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# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	mb	E
2	С	collector		в -{*
3	E	emitter		C; mb
mb	С	mounting base; connected to collector	DPAK (SOT428C)	aaa-029889

## 6. Ordering information

### **Table 3. Ordering information**

Table of ordering information						
Type number	Package					
	Name	Description	Version			
MJD44H11A	DPAK	Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428C			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
MJD44H11A	MJD44H11A

# 8. Limiting values

### Table 5. Limiting values

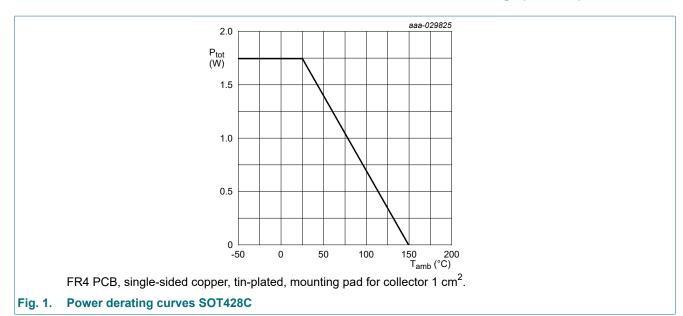
In accordance with the Absolute Maximum Rating System (IEC601134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CEO}$	collector-emitter voltage			-	80	V
$V_{EBO}$	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	8	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	16	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C	[1]	-	20	W
		T <sub>amb</sub> ≤ 25 °C	[2]	-	1.75	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Total power dissipation junction to mounting base.

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

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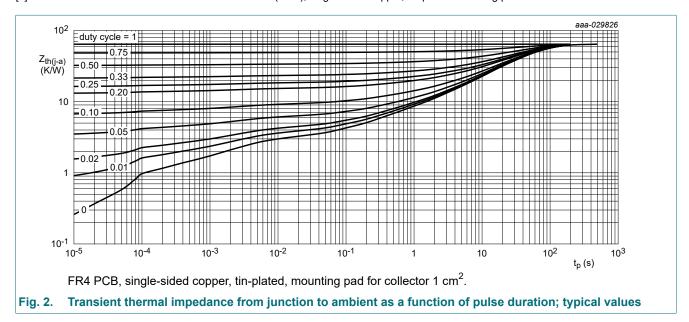


### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	in free air		-	-	6.25	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		[1]	-	-	72	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.



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## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CES</sub> collector-er	collector-emitter cut-off	V <sub>CE</sub> = 64 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	1	μΑ
	current	V <sub>CE</sub> = 64 V; V <sub>BE</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	1	μΑ
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1 V; I <sub>C</sub> = 2 A; T <sub>amb</sub> = 25 °C	60	-	-	
		V <sub>CE</sub> = 1 V; I <sub>C</sub> = 4 A; T <sub>amb</sub> = 25 °C	40	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 8 A; I <sub>B</sub> = 400 mA; T <sub>amb</sub> = 25 °C	-	-	1	V
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 8 A; I <sub>B</sub> = 800 mA; T <sub>amb</sub> = 25 °C	-	-	1.5	V
t <sub>on</sub>	turn-on time	I <sub>C</sub> = 5 A; I <sub>Bon</sub> = 0.5 mA; I <sub>Boff</sub> = -0.5 mA;	-	300	-	ns
t <sub>s</sub>	storage time	V <sub>CC</sub> = 12.5 V; T <sub>amb</sub> = 25 °C	-	250	-	ns
t <sub>f</sub>	fall time		-	170	-	ns
t <sub>off</sub>	turn-off time		-	420	-	ns
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25  ^{\circ}\text{C}$	-	30	-	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	160	-	MHz

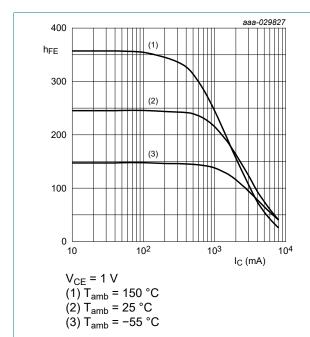


Fig. 3. DC current gain as a function of collector current; typical values

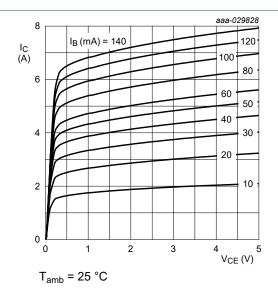
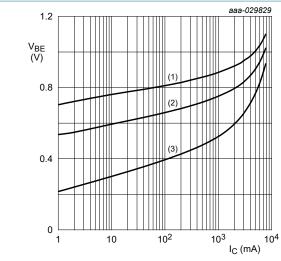


Fig. 4. Collector current as a function of collectoremitter voltage; typical values

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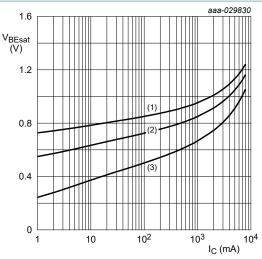


$$V_{CE} = 5 V$$

$$(1) T_{amb} = -55 ° ($$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 5. Base-emitter voltage as a function of collector current; typical values



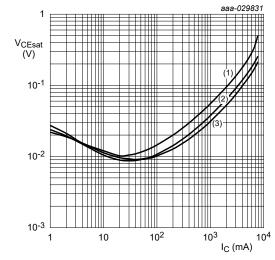
$$I_{\rm C}/I_{\rm B} = 10$$

$$I_{C}/I_{B} = 10$$
  
(1)  $T_{amb} = -55 \,^{\circ}C$   
(2)  $T_{amb} = 25 \,^{\circ}C$   
(3)  $T_{amb} = 150 \,^{\circ}C$ 

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

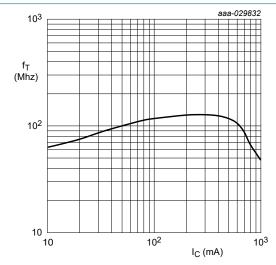


$$I_{\rm C}/I_{\rm B}=20$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

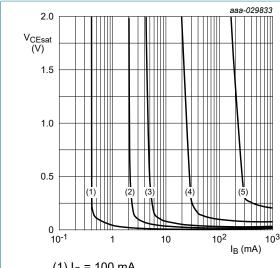
Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



$$V_{CE}$$
 = 2 V  
 $T_{amb}$  = 25 °C

Fig. 8. Transition frequency as a function of collector current; typical values

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(1)  $I_C = 100 \text{ mA}$ (2)  $I_C = 500 \text{ mA}$ 

 $(3) I_C = 1000 \text{ mA}$ 

 $(4) I_C = 3000 \text{ mA}$  $(5) I_C = 8000 \text{ mA}$ 

Collector-emitter saturation region as a function Fig. 9. of base current; typical values

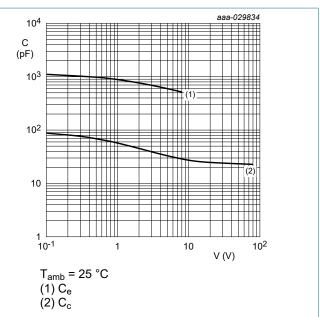
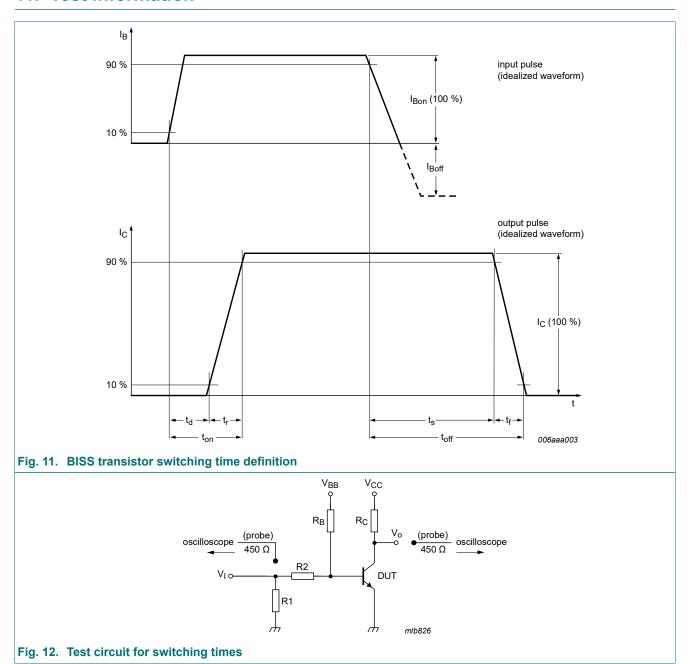


Fig. 10. Input/output capacitance as a function of input/ output voltage

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## 11. Test information

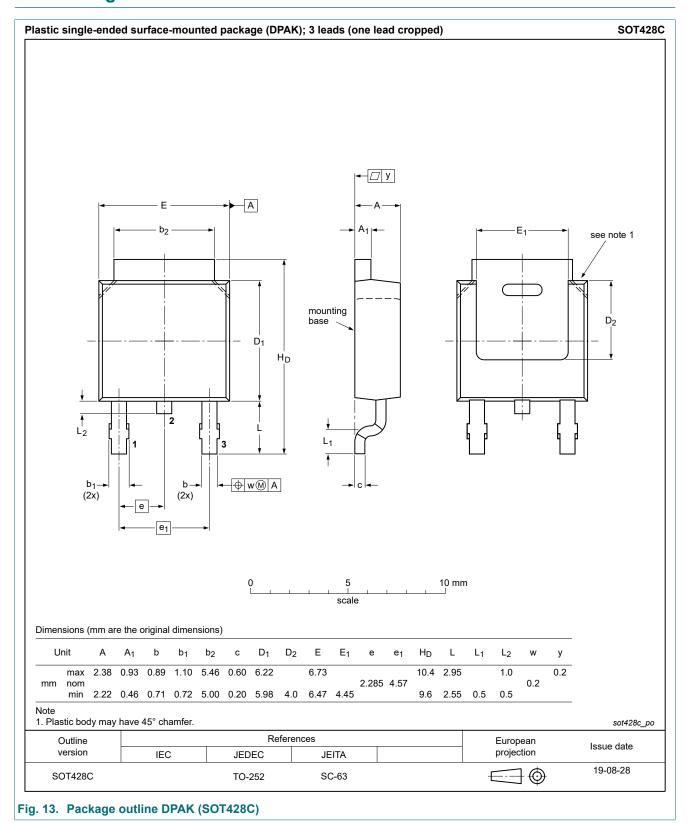


### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

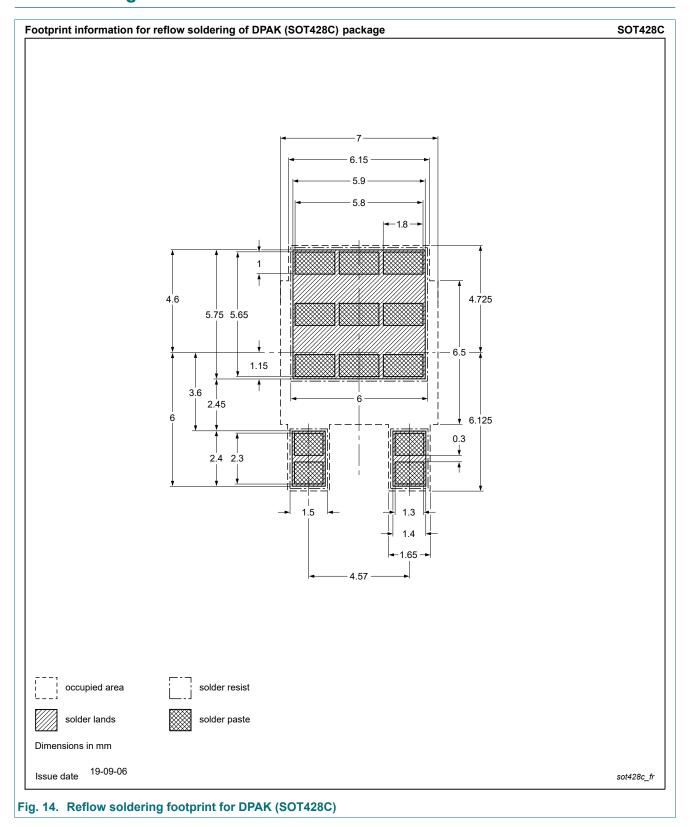
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# 12. Package outline



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# 13. Soldering



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# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
MJD44H11A v.3	20190912	Product data sheet	-	MJD44H11A v.2			
Modifications:	Package outline ada	Package outline adapted to SOT428C					
MJD44H11A v.2	20190729	Product data sheet	-	MJD44H11A v.1			
MJD44H11A v.1	20190528	Preliminary data sheet	-	-			

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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